1HN04CH



http://onsemi.com

Power MOSFET 100V, 8Ω , 270mA, Single N-Channel

Features

• 4V drive

• Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	V _{DSS}		100	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		270	mA
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	1080	mA
Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	0.6	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm²×0.8mm)	$R_{ heta JA}$	208	°C/W

Electrical Characteristics at Ta = 25°C

Dorometer	Symbol	Conditions	Value			11.7
Parameter			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =100V, V _{GS} =0V			1	μА
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μА
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =100μA	1.2		2.6	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =140mA		260		mS
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =140mA, V _{GS} =10V		6	8	Ω
	R _{DS} (on)2	I _D =70mA, V _{GS} =4V		6.8	9.8	Ω
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		15		pF
Output Capacitance	Coss			3.1		pF
Reverse Transfer Capacitance	Crss			0.9		pF

Continued on next page.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

^{*} Machine Model

1HN04CH

Continued from preceding page.

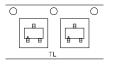
Parameter	Symbol	O an distance	Value			Linit
		Conditions	min	typ	max	Unit
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		10		ns
Rise Time	t _r			7.4		ns
Turn-OFF Delay Time	t _d (off)			58		ns
Fall Time	tf			39		ns
Total Gate Charge	Qg	V _{DS} =50V, V _{GS} =10V, I _D =270mA		0.9		nC
Gate to Source Charge	Qgs			0.19		nC
Gate to Drain "Miller" Charge	Qgd			0.26		nC
Forward Diode Voltage	V _{SD}	I _S =270mA, V _{GS} =0V	•	0.88	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Ordering & Package Information

Device	Package	Shipping	note
1HN04CH-TL-W	CPH3, SC-59 SOT-23, TO-236	3,000 pcs. / reel	Pb-Free and Halogen Free

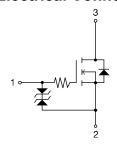
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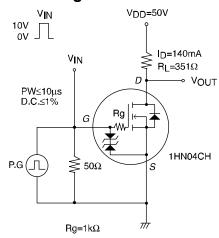
Marking

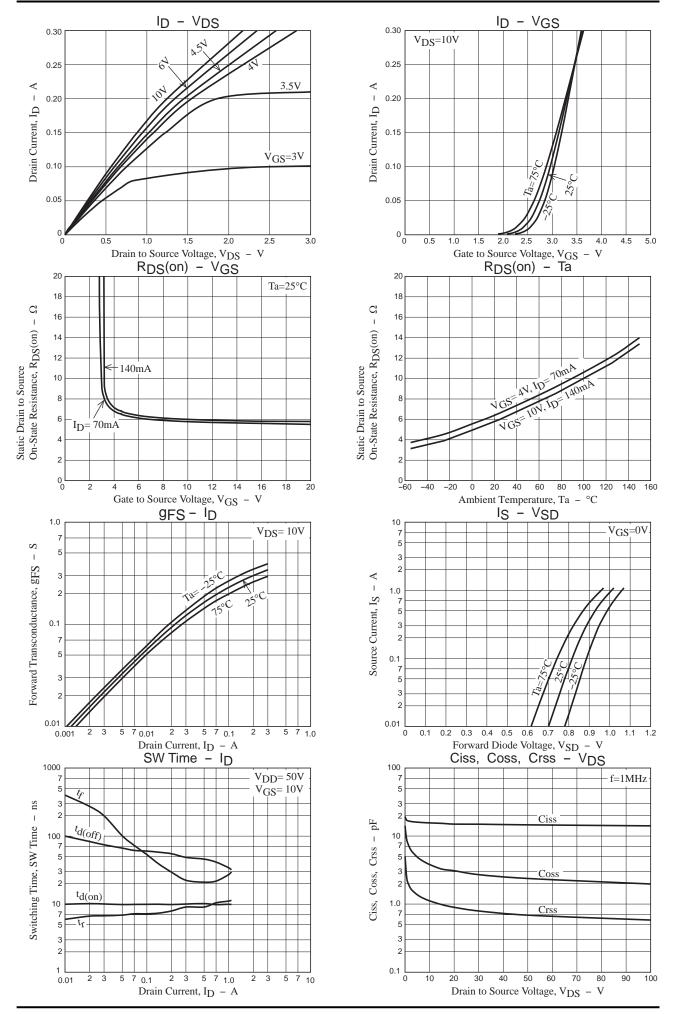


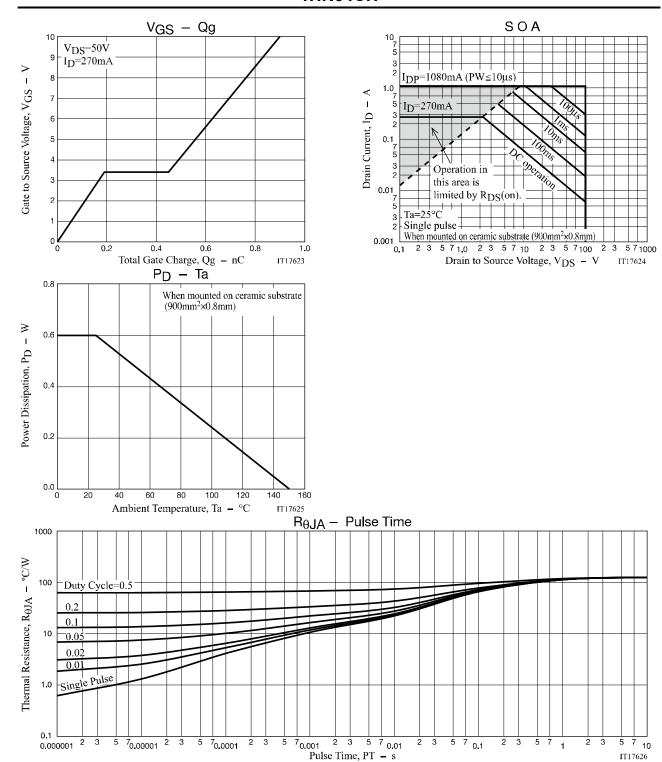
Electrical Connection



Switching Time Test Circuit







Package Dimensions

1HN04CH-TL-W

CPH3

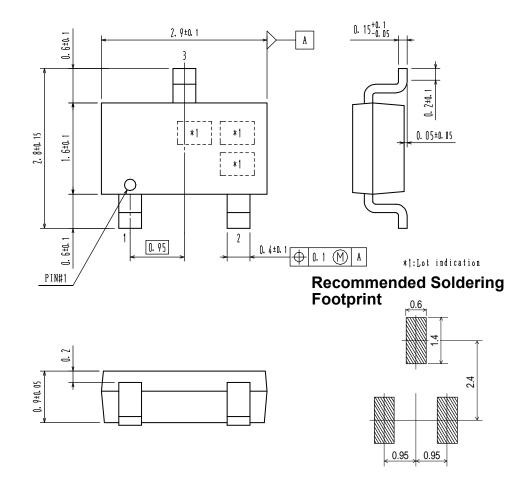
CASE 318BA ISSUE O

unit: mm

1: Gate

2: Source

3: Drain



Note on usage: Since the 1HN04CH is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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